

Gate resistor installed Dual N-channel MOSFET

KFCAB21520L Data Sheet

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1. GENERAL DESCRIPTION

Gate resistor installed Dual N-channel MOSFET

For lithium-ion secondary battery protection circuits

2. FEATURES

- Source-source ON resistance: $R_{SS}(\text{on})$ typ. = 1.6 m Ω ($V_{GS} = 3.8$ V)
- CSP (Chip Size Package)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL: Level 1)

3. MARKING SYMBOL: 7T

4. PACKAGING

Embossed type (Thermo-compression sealing): 8,000 pcs / reel (standard)

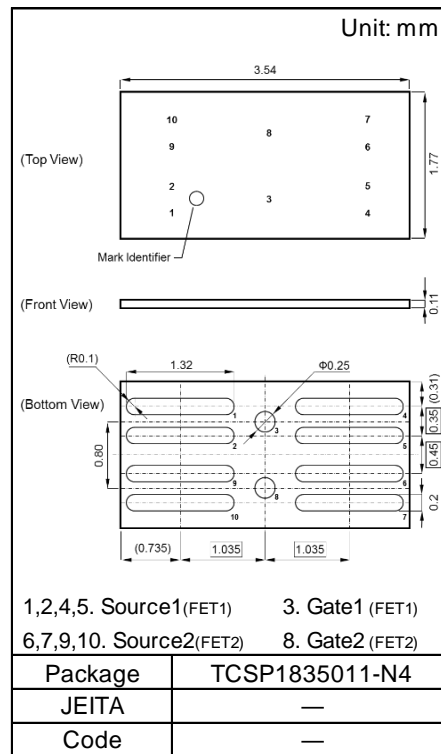
5. ABSOLUTE MAXIMUM RATINGS $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Source-source Voltage	VSS	12	V
Gate-source Voltage	VGS	± 8	V
Source Current	DC ^{*1}	IS1	16
	DC ^{*2}	IS2	35
	Pulse ^{*3}	ISp	160
Total Power Dissipation	DC ^{*1}	PD1	0.54
	DC ^{*2}	PD2	3.8
Channel Temperature	Tch	150	$^\circ\text{C}$
Storage Temperature Range	Tstg	-55 to +150	$^\circ\text{C}$

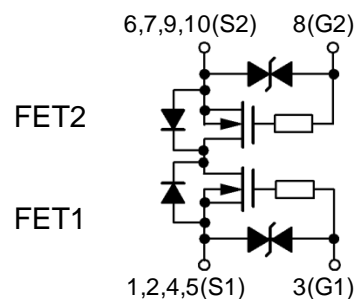
6. THERMAL CHARACTERISTICS $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Thermal Resistance (ch-a)	Rth1 ^{*1}	232	$^\circ\text{C} / \text{W}$
	Rth2 ^{*2}	33	$^\circ\text{C} / \text{W}$

- Note
- *1 Mounted on FR4 board (25.4 mm x 25.4 mm x t1.0 mm) using the minimum recommended pad size (36 μm Copper).
 - *2 Mounted on Ceramic substrate (70 mm x 70 mm x t1.0 mm).
 - *3 $t = 10$ μs , Duty Cycle $\leq 1\%$



Equivalent Circuit



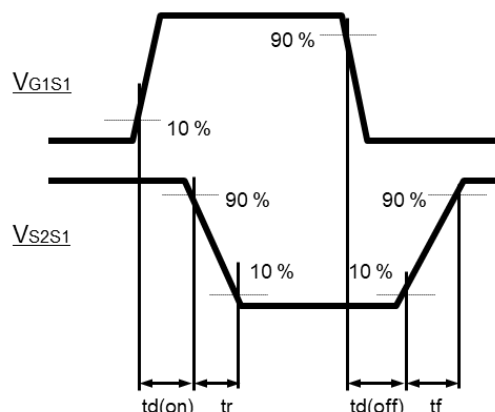
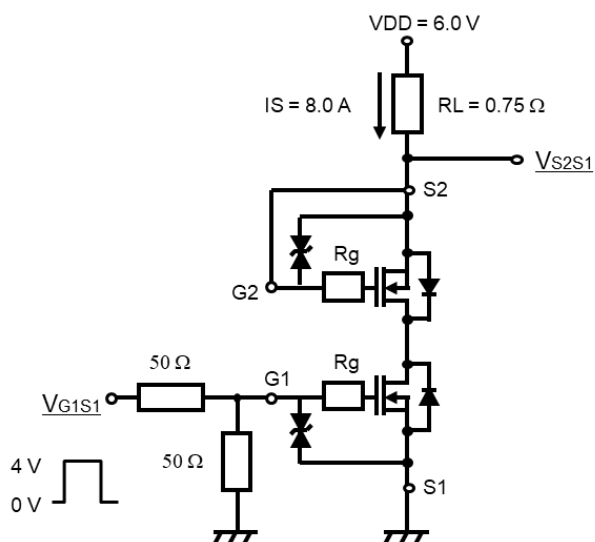
7. ELECTRICAL CHARACTERISTICS $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Source-source Breakdown Voltage	VSSS	$I_S = 1\text{ mA}$, $V_{GS} = 0\text{ V}$	12			V
Zero Gate Voltage Source Current	ISSS	$V_{SS} = 12\text{ V}$, $V_{GS} = 0\text{ V}$			1.0	μA
Gate-source Leakage Current	IGSS	$V_{GS} = \pm 8\text{ V}$, $V_{SS} = 0\text{ V}$			± 10	μA
		$V_{GS} = \pm 5\text{ V}$, $V_{SS} = 0\text{ V}$			± 1.0	
Gate-source Threshold Voltage	V_{th}	$I_S = 1.64\text{ mA}$, $V_{SS} = 10\text{ V}$	0.35	0.90	1.40	V
Source-source On-state Resistance	RSS(on)1	$I_S = 8.0\text{ A}$, $V_{GS} = 4.5\text{ V}$	1.10	1.45	2.00	$\text{m}\Omega$
	RSS(on)2	$I_S = 8.0\text{ A}$, $V_{GS} = 3.8\text{ V}$	1.15	1.60	2.10	
	RSS(on)3	$I_S = 8.0\text{ A}$, $V_{GS} = 3.1\text{ V}$	1.20	1.80	3.00	
	RSS(on)4	$I_S = 8.0\text{ A}$, $V_{GS} = 2.5\text{ V}$	1.40	2.30	4.50	
Body Diode Forward Voltage	$V_{F(s-s)}$	$I_F = 8.0\text{ A}$, $V_{GS} = 0\text{ V}$		0.7	1.2	V
Input Capacitance *1	Ciss	$V_{SS} = 10\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ kHz}$		5250		pF
Output Capacitance *1	Coss			700		
Reverse Transfer Capacitance *1	Crss			630		
Turn-on Delay Time *1,*2	$t_{d(on)}$	$V_{DD} = 6.0\text{ V}$, $V_{GS} = 0\text{ to }4\text{ V}$ $I_S = 8.0\text{ A}$		1.5		μs
Rise Time *1,*2	t_r			2.6		
Turn-off Delay Time *1,*2	$t_{d(off)}$	$V_{DD} = 6.0\text{ V}$, $V_{GS} = 4\text{ to }0\text{ V}$ $I_S = 8.0\text{ A}$		6.8		μs
Fall Time *1,*2	t_f			4.1		
Total Gate Charge *1	Qg	$V_{DD} = 6.0\text{ V}$		38		nC
Gate-source Charge *1	Qgs	$V_{GS} = 0\text{ to }4\text{ V}$		20		
Gate-drain Charge *1	Qgd	$I_S = 8.0\text{ A}$		10		

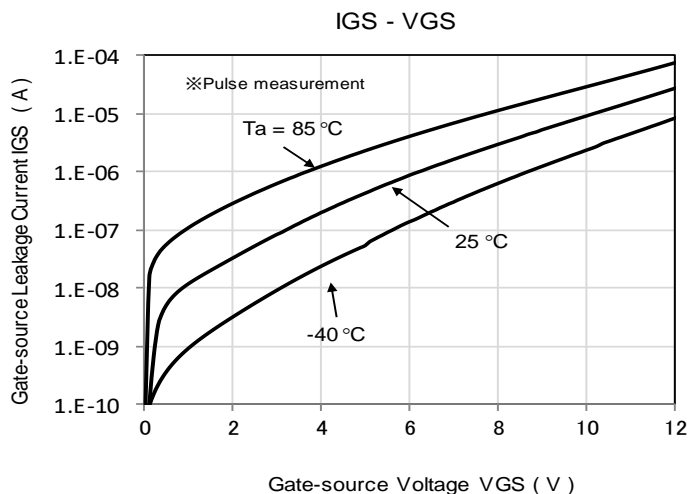
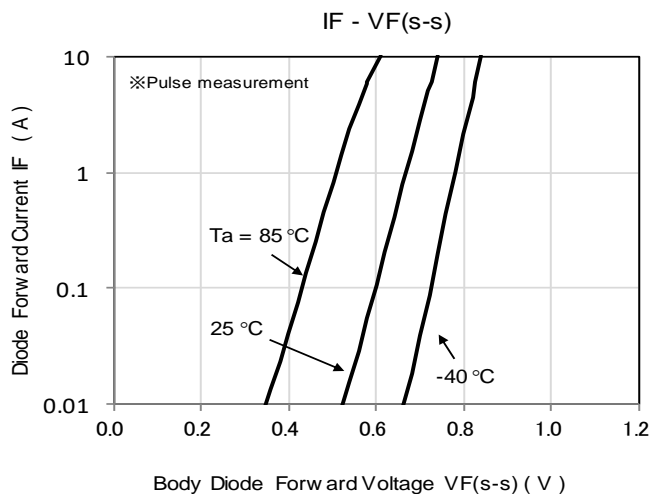
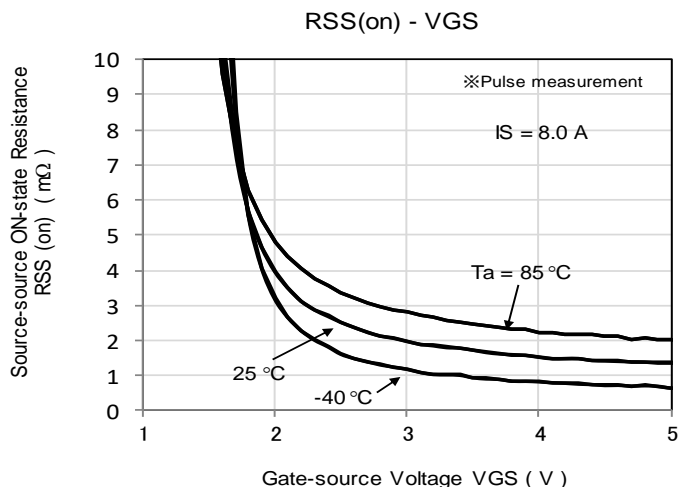
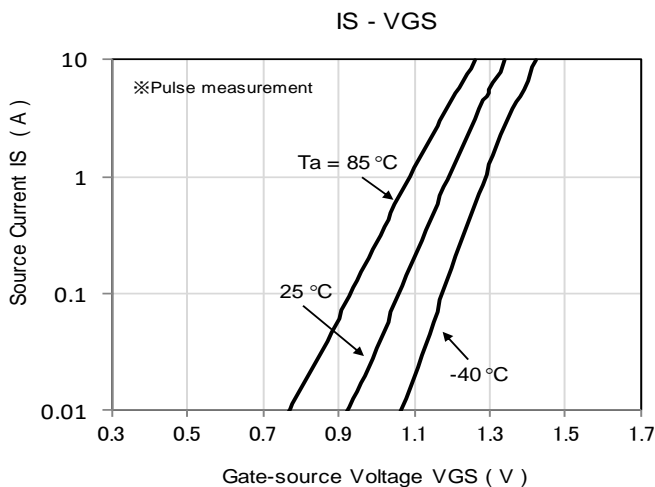
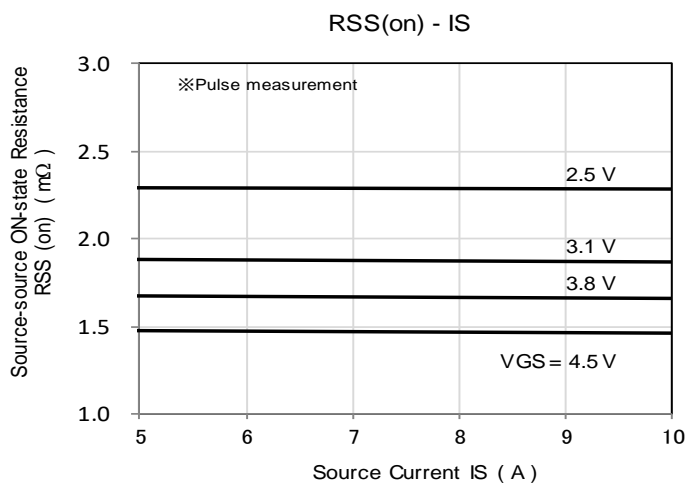
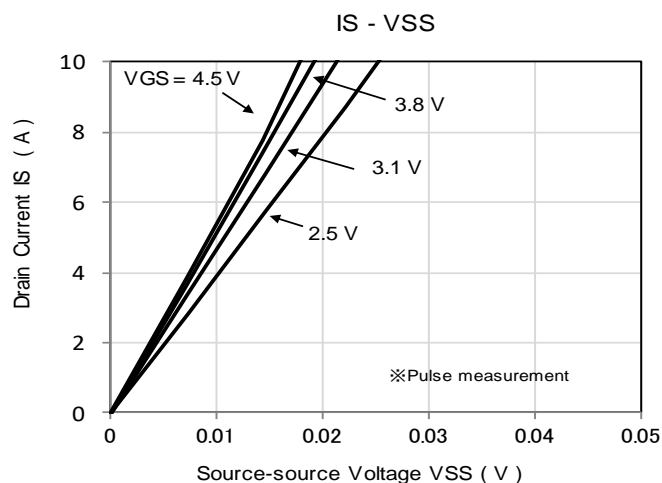
Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

*1 Guaranteed by design, not subject to production testing

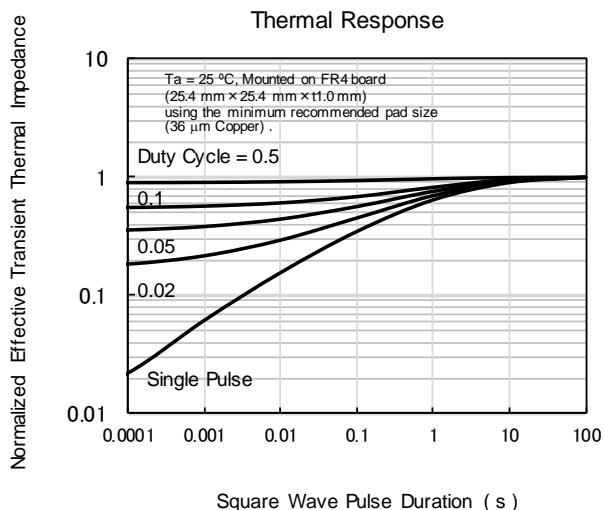
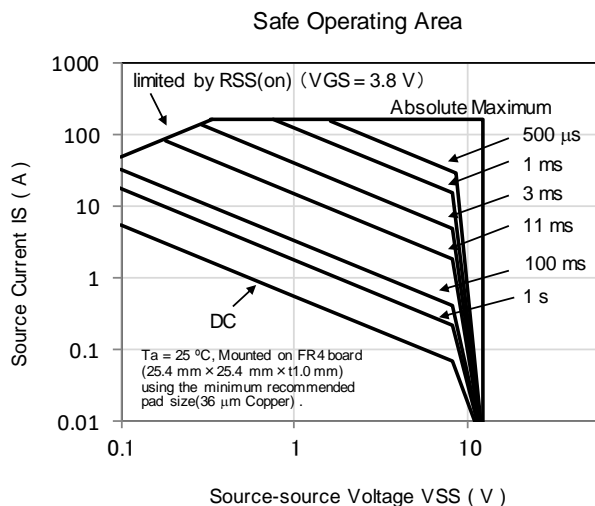
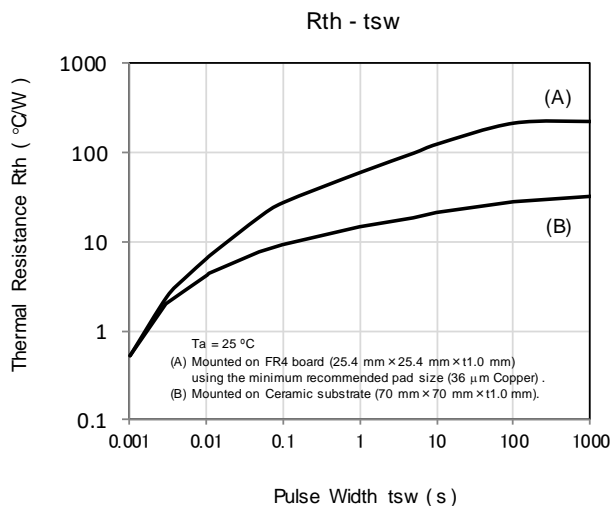
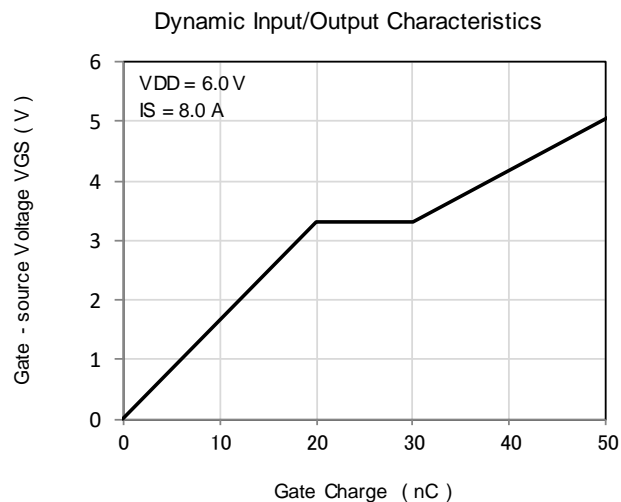
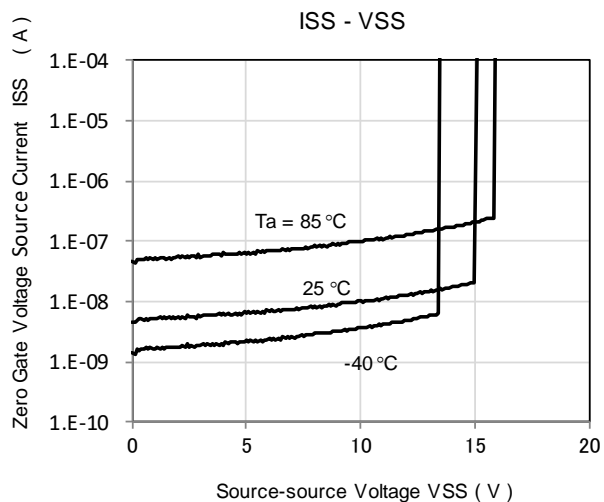
*2 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time



8. TECHNICAL DATA (Reference)

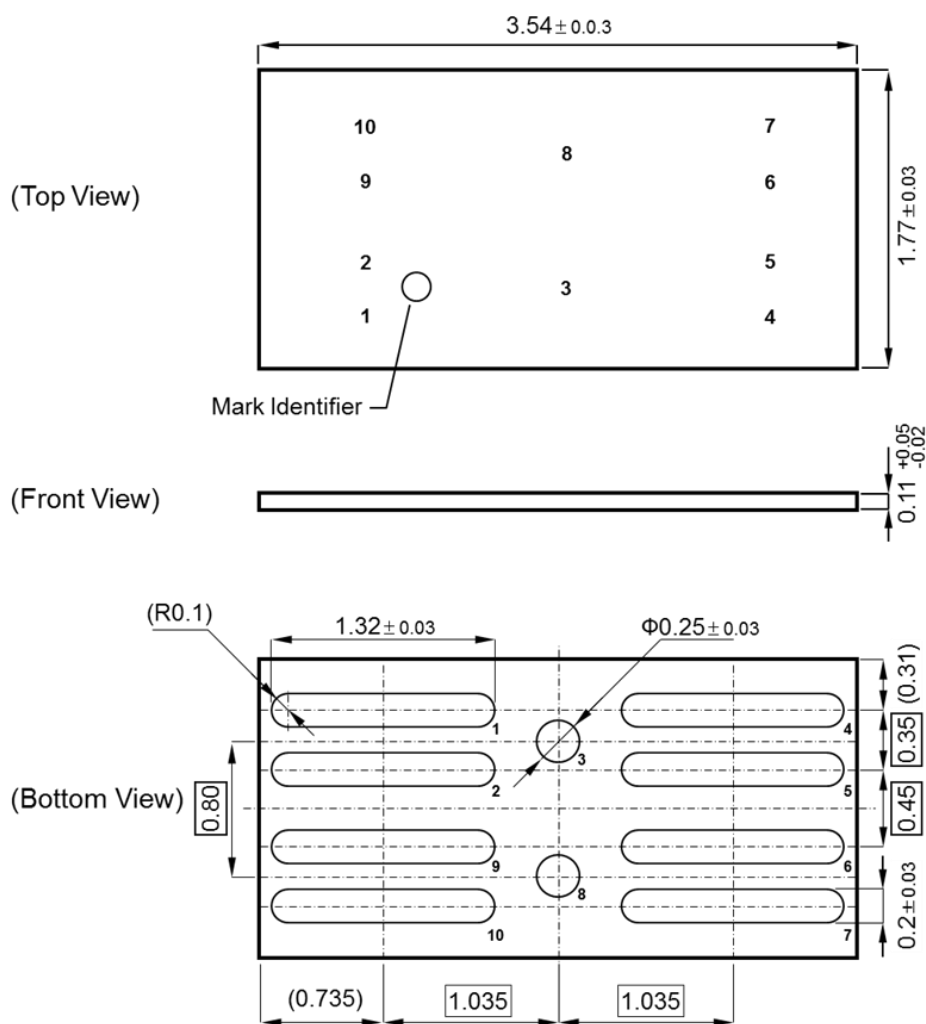


TECHNICAL DATA (Reference)



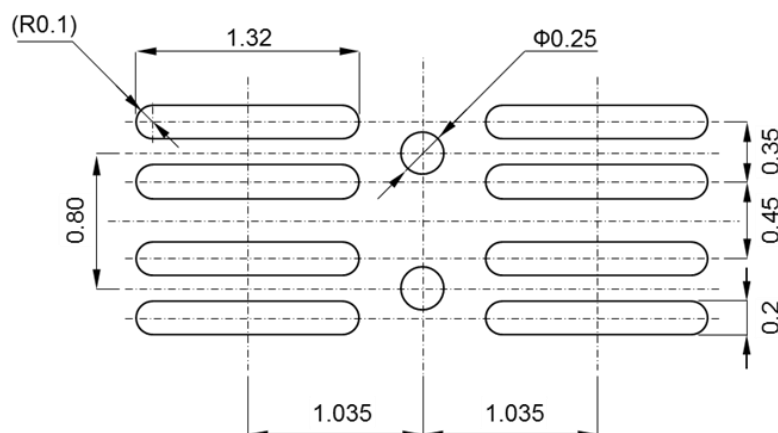
9. OUTLINE

Unit : mm



10.LAND PATTERN (Reference)

Unit : mm



11. REVISION HISTORY

Date	Revision	Description
2021.2.3	1.00	1. initially issued.

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